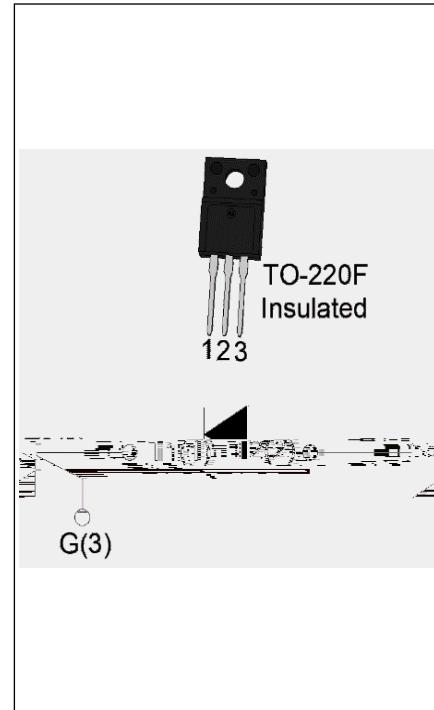


**DESCRIPTION:**

The JST24F-800B triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. By using an external plastic package, JST24F-800B provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	25	A
V_{DRM}/V_{RRM}	800	V
$I_{GT\text{ I/II/III/IV}}$	50/50/50/70	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c \leq 72^\circ\text{C}$)	$I_{T(RMS)}$	25	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	250	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		275	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	340	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	dI/dt	100	$\text{A}/\mu\text{s}$
		50	
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W



Peak pulse voltage (T _j =25°C; non-repetitive,off-state;FIG.7)	V _{pp}	2	kV
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ELECTRICAL CHARACTERISTICS (T_j=25°C unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I _{GT}	V _D =12V R _L =33	I - II -III	MAX.	50	mA
		IV		70	
V _{GT}		ALL	MAX.	1	V
V _{GD}	V _D =V _{DRM} T _j =125°C R _L =3.3K	ALL	MIN.	0.2	V
I _L	I _G =1.2I _{GT}	I - III-IV	MAX.	80	mA
		II		120	
I _H	I _T =500mA		MAX.	80	mA
dV/dt	V _D =540V Gate Open T _j =125°C		MIN.	1000	V/μs
(dV/dt)c	(dI/dt)c=13.3A/ms, T _j =125°C		MIN.	12	V/μs
t _{on}	I _G =80mA I _A =400mA I _R =40mA T _j =25°C	TYP.	3	μs	
t _{off}			50		

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V _{TM}	I _{TM} =35A t _p =380μs	T _j =25°C	1.5	V
V _{TO}	Threshold voltage	T _j =125°C	0.75	V
R _D	Dynamic resistance	T _j =125°C	18	m
I _{DRM}	V _D =V _{DRM} V _R =V _{RRM}	T _j =25°C	5	μA
I _{RRM}		T _j =125°C	2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-c)}	junction to case (AC)	1.5	°C/W
R _{th(j-a)}	junction to ambient (AC)	60	°C/W

**ORDERING INFORMATION**

J	ST	24	F	-800	B
JieJie Microelectronics Co., Ltd.					
	Triacs				
		IT(RMS):25A			
			F:TO-220F(Ins)		
				B:IGT1-3≤50mA IGT4≤70mA	
					800:VDRM / VRRM ≥800V

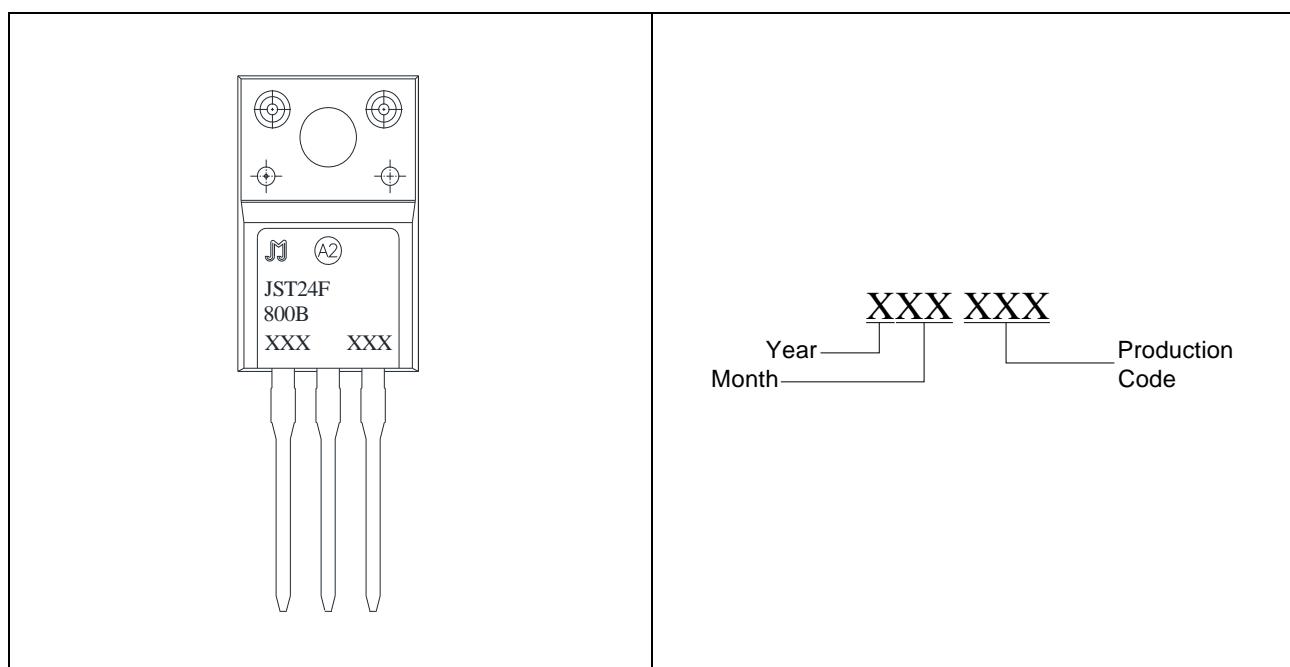
MARKING



FIG.1 Maximum power dissipation versus RMS on-state current

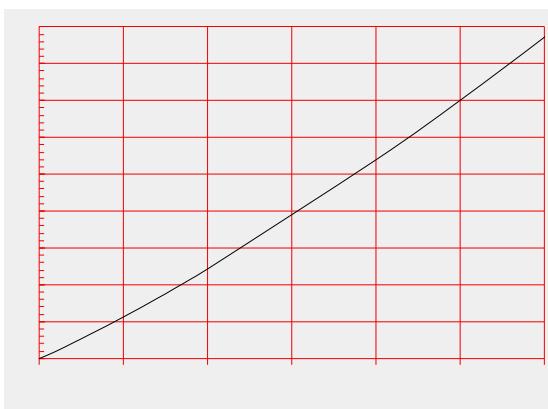


FIG.3: Surge peak on-state current versus number of cycles

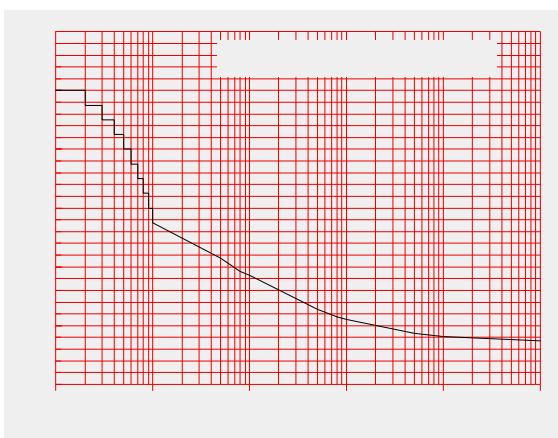


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t (I - II : $dI/dt < 100\text{A}/\mu\text{s}$; III-IV : $dI/dt < 50\text{A}/\mu\text{s}$)

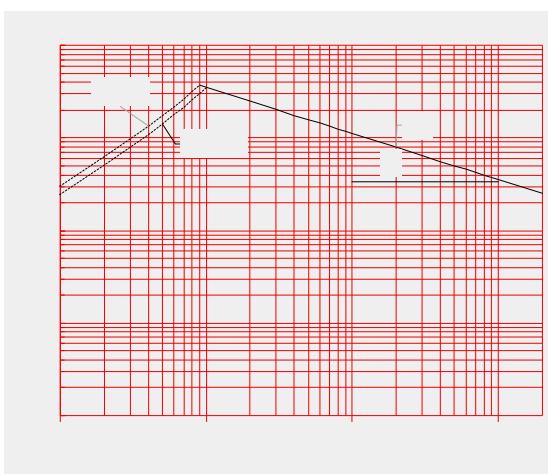


FIG.2: RMS on-state current versus case temperature

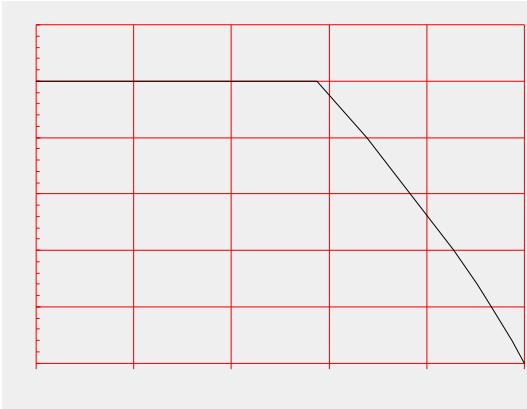


FIG.4: On-state characteristics

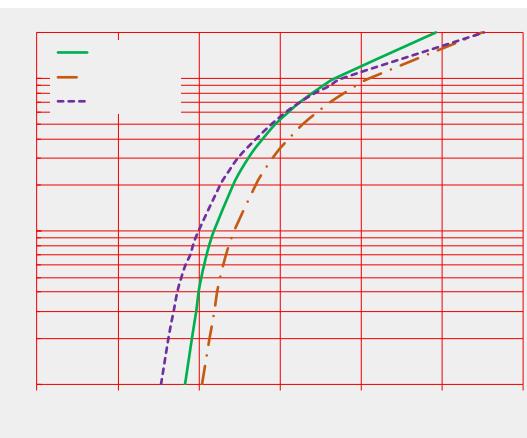


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

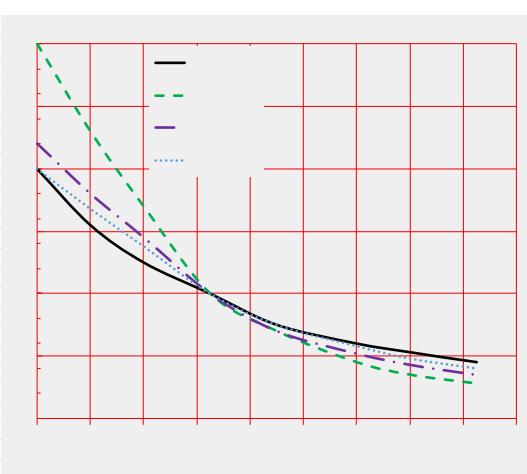
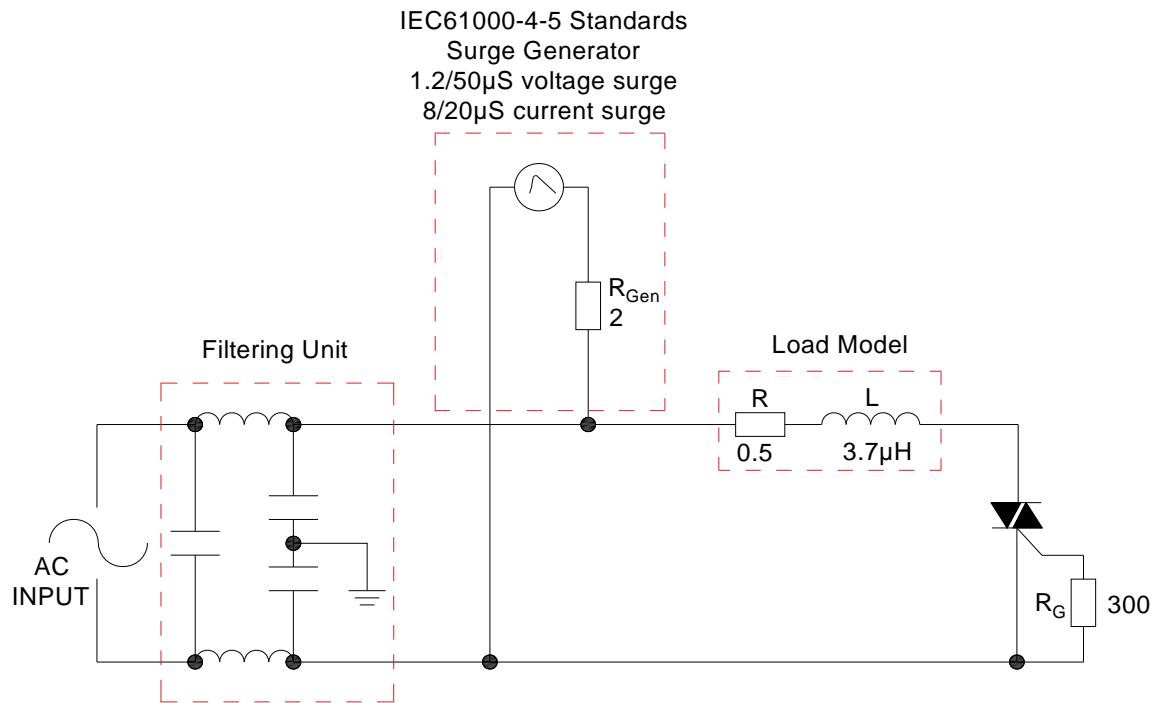




FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie.

**ORDERING INFORMATION**

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		-	-			
JST24F-800B	800	50	70	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated



PACKAGE MECHANICAL DATA





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